Module Features

- 4x128Kx64 Synchronous
- Flow-Through Architecture
- Clock Controlled Registered Bank Enables (E1\, E2\, E3, E4\)
- Clock Controlled Registered Address
- Clock Controlled Registered Global Write (GW\)
- Aysnchronous Output Enable (G\)
- Internally self-timed Write
- Module Sleep Mode enable (ZZ)
- Gold Lead Finish
- 3.3V ±10% Operation
- Access Speed(s): TKHQV=9.5, 10, 11, 12, 15ns
- Common Data I/O
- High Capacitance (30pf) drive, at rated Access Speed
- Single total array Clock
- Multiple Vcc and Gnd

4x128Kx64, 3.3V Synchronous Flow-Through

The EDI2KG64128VxxD is a Synchronous SRAM, 60 position Card Edge DIMM (120 contacts) Module, organized as 4x128Kx64. The Module contains eight (8) Synchronous Burst Ram Devices, packaged in the industry standard JEDEC 14mmx20mm TQFP placed on a Multilayer FR4 Substrate. The module architecture is defined as a Synchronous Only, Flow-Through, Early Write Device. This module provides High Performance, Ultra Fast access times at a cost per bit benefit over BiCMOS Asynchronous SRAM based devices. As well as improved cost per bit, the use of Synchronous or Synchronous Burst devices or modules can ease the memory subsystem design by reducing or easing the memory controller requirement.

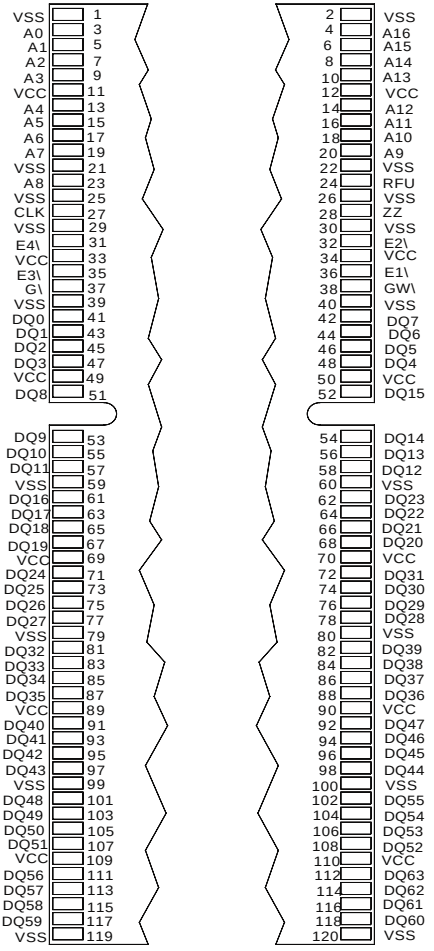
Synchronous operations are in relation to an externally supplied clock, Registered Address, Registered Global Write, Registered Enables as well as an Asynchronous Output enable. All read and write operations to this module are performed on Quad Words (64 bit operations).

Write cycles are internally self timed and are initiated by a rising clock edge. This feature relieves the designer the task of developing external write pulse width circuitry.

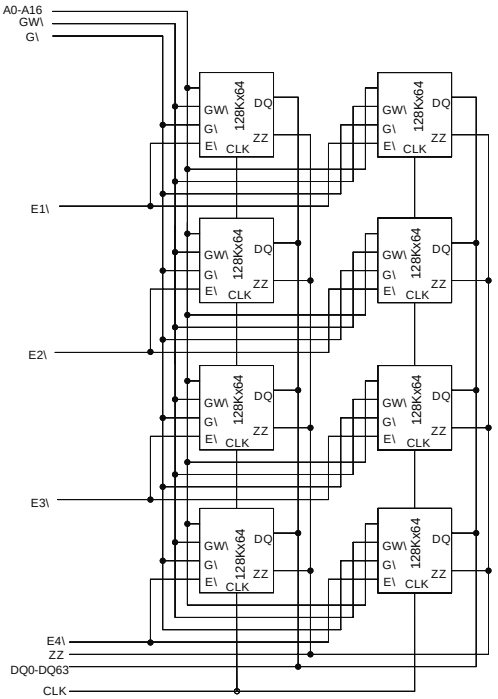
Pin Names

DQ0-DQ63	Input/Output Bus
A0-A15	Address Bus
E1\, E2\, E3\, E4\	Synchronous Bank Enables
Clk	Array Clock
GW\	Synchronous Global write Enable
G\	Asynchronous Output Enable
ZZ	Module Sleep Enable
Vcc	3.3V Power Supply
Vss	Gnd

Pin Configuration



Functional Block Diagram



EDI2KG464128V
4 Megabyte Synchronous
Card Edge DIMM

Pin Descriptions

DIMM Pins	Symbol	Type	Description
3, 5, 7, 9, 15, 17, 1 9, 23, 20, 18, 16, 14, 10, 8, 6, 4	A0-A16	Input Synchronous	Addresses: These inputs are registered and must meet the setup and hold times around the rising edge of CLK. The burst counter generates internal addresses associated with A0 and A1, during burst and wait cycle.
38	GW\	Input Synchronous	Global Write: This active LOW input allows a full 72-bit WRITE to occur independent of the BWE\ and BWx\ lines and must meet the setup and hold times around the rising edge of CLK.
27	CLK	Input Synchronous	Clock: This signal registers the addresses, data, chip enables, write control and burst control inputs on its rising edge. All synchronous inputs must meet setup and hold times around the clock's rising edge.
36, 32, 35, 31	E1\, E2\ E3\, E4\	Input Synchronous	Bank Enables: These active LOW inputs are used to enable each individual bank and to gate ADSP\.
37	G\	Input	Output Enable: This active LOW asynchronous input enables the data output drivers.
	ZZ	Input Asynchronous	Module Snooze: This active high signal places the memory module in sleep mode (low power consumption).
Various	DQ0-63	Input/Output	Data Inputs/Outputs: First byte is DQ0-7, second byte is DQ8-15, third byte is DQ16-23, fourth byte is DQ24-31, fifth byte is DQ32-39, sixth byte is DQ40-47, seventh byte is DQ48-55 and the eight byte is DQ56-64.
Various	Vcc	Supply	Core power supply: +3.3V -5%/+10%
Various	Vss	Ground	Ground

Synchronous Only - Truth Table

Operation	E1\	E2\	E3\	E4\	GW\	G\	ZZ	CLK	DQ
Synchronous Write-Bank 1	L	H	H	H	L	H	L	↑	High-Z
Synchronous Read-Bank 1	L	H	H	H	H	L	L	↑	
Synchronous Write-Bank 2	H	L	H	H	L	H	L	↑	High-Z
Synchronous Read-Bank 2	H	L	H	H	H	L	L	↑	
Synchronous Write-Bank 3	H	H	L	H	L	H	L	↑	High-Z
Synchronous Read-Bank 3	H	H	L	H	H	L	L	↑	
Synchronous Write-Bank 4	H	H	H	L	L	H	L	↑	High-Z
Synchronous Read-Bank 4	H	H	H	L	H	L	L	↑	
Snooze Mode	X	X	X	X	X	X	H	X	High-Z

*Absolute Maximum Ratings**

Voltage on Vcc Relative to Vss	-0.5V to +4.6V
Vin	-0.5V to Vcc +0.5V
Storage Temperature	-55°C to +125°C
Operating Temperature (Commercial)	0°C to +70°C
Operating Temperature (Industrial)	-40°C to +85°C
Short Circuit Output Current	10 mA

*Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions greater than those indicated in operational sections of this specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

AC Test Conditions

Input Pulse Levels	Vss to 3.0V
Input and Output Timing Ref.	1.25V
Output Test equivalencies	

AC Test Load

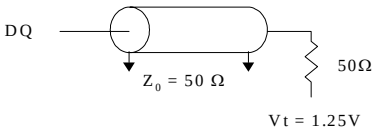


Fig. 1 Output Load Equivalent

Recommended DC Operating Conditions

Parameter	Sym	Min	Typ	Max	Units
Supply Voltage	VCC	3.14	3.3	3.6	V
Supply Voltage	VSS	0.0	0.0	0.0	V
Input High	VIH	1.1	3.0	VCC+0.3	V
Input Low	VIL	-0.3	0.0	0.3	V
Input Leakage	ILi	-2	1	2	µA
Output Leakage	ILo	-2	1	2	µA

DC Electrical Characteristics - Read Cycle

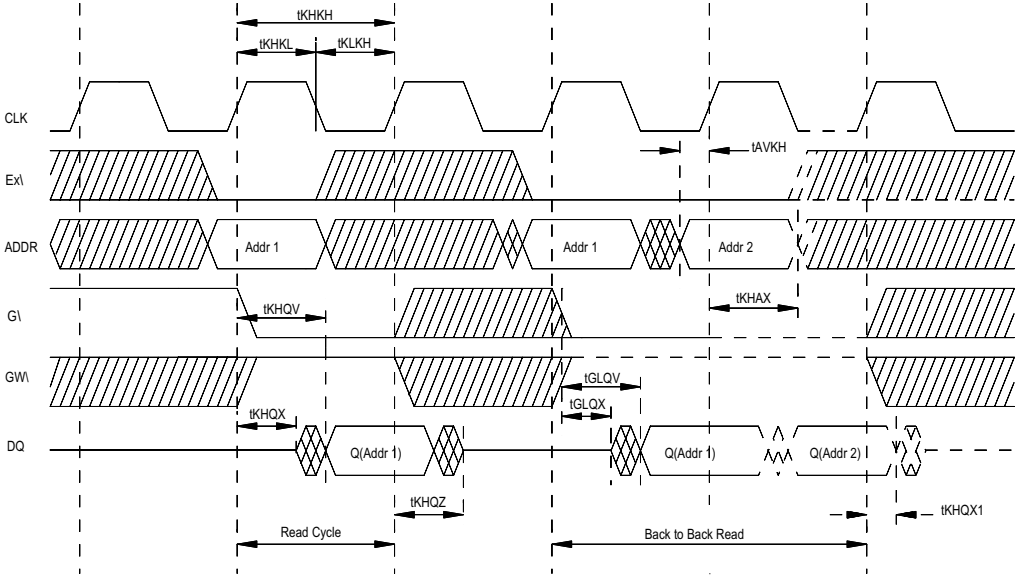
			Max					
Description	SYM	Typ	9.5	10	11	12	15	Units
Power Supply Current	Icc1	1.55	2.8	2.2	2.2	2.7	2.0	A
Power Supply Current Device Selected,No Operation	Icc	.750	1.8	1.5	1.3	1.3	1.0	A
Snooze Mode	IccZZ	200	300	300	300	300	300	mA
CMOS Standby	Icc3	400	500	500	500	500	500	mA
Clock Running-Deselect	IccK	600	900	900	900	900	900	mA

Read Cycle Timing Parameters

		9.5ns		10ns		11ns		12ns		15ns		
Description	Sym	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Units
Clock Cycle Time	tKhKh	*	*	12		13		15		20		ns
Clock High Time	tKHKL	*	*	5		5		5		6		ns
Clock Low Time	tKLKH	*	*	5		5		5		6		ns
Clock to Output Valid	tKHQV	*	*		10		11		12		15	ns
Clock to Output Invalid	tKHQX1	*	*	3		3		3		3		ns
Clock to Output Low-Z	tKHQX	*	*	2		2		2		2		ns
Output Enable to Output Valid	tGLQV	*	*		4		5		5		6	ns
Output Enable to Output Low-Z	tGLQX	*	*	0		0		0		0		ns
Output Enable to Output High-Z	tGHQZ	*	*		4		5		5		5	ns
Address Setup	tAVKH	*	*	2.5		2.5		2.5		2.5		ns
Bank Enable Setup	tEVKH	*	*	2.5		2.5		2.5		2.5		ns
Address Hold	tKHAX	*	*	1.0		1.0		1.0		1.0		ns
Bank Enable Hold	tKHEX	*	*	1.0		1.0		1.0		1.0		ns

*TBD

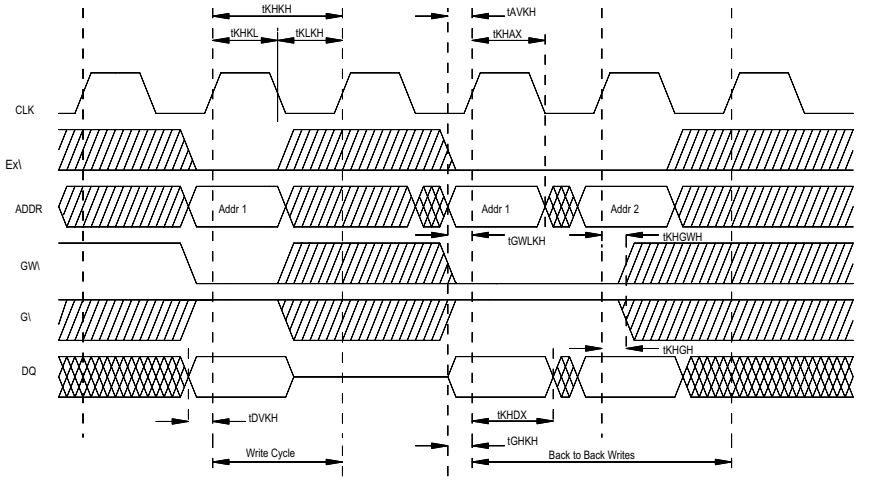
Synchronous Read Cycle



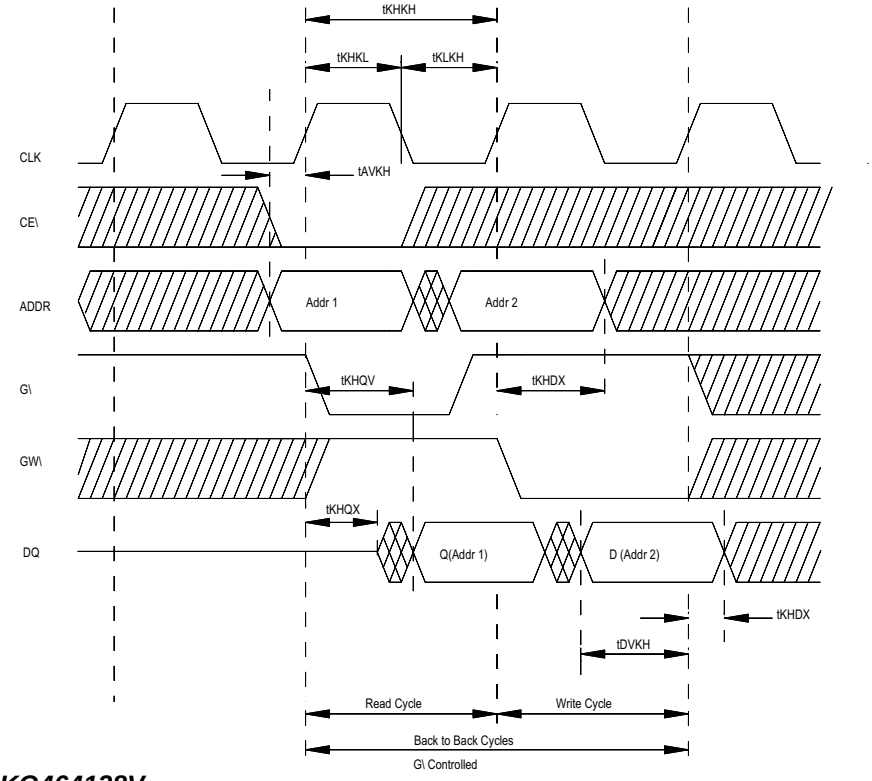
Write Cycle Timing Parameters

		9.5ns		10ns		11ns		12ns		15ns		
Description	**Sym**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Units**
Clock Cycle Time	tKHKH	*	*	12		13		15		20		ns
Clock High Time	tKHKL	*	*	5		5		5		6		ns
Clock Low Time	tKLKH	*	*	5		5		5		6		ns
Address Setup	tAVKH	*	*	2.5		2.5		2.5		2.5		ns
Address Hold	tKHAX	*	*	1.0		1.0		1.0		1.0		ns
Bank Enable Setup	tEVKH	*	*	2.5		2.5		2.5		2.5		ns
Bank Enable Hold	tKHEX	*	*	1.0		1.0		1.0		1.0		ns
Global Write Enable Setup	tWVKH	*	*	2.5		2.5		2.5		2.5		ns
Global Write Enable Hold	tKHWX	*	*	1.0		1.0		1.0		1.0		ns
Data Setup	tDVKH	*	*	2.5		2.5		2.5		2.5		ns
Data Hold	tKHDX	*	*	1.0		1.0		1.0		1.0		ns

Sync Write Cycle



Sync Read/Write Cycle



Ordering Information

Part Number	Organization	Voltage	Speed (ns)	Package
EDI2KG464128V95D*	4x128Kx64	3.3	9.5	120 Card Edge DIMM
EDI2KG464128V10D*	4x128Kx64	3.3	10	120 Card Edge DIMM
EDI2KG464128V11D	4x128Kx64	3.3	11	120 Card Edge DIMM
EDI2KG464128V12D	4x128Kx64	3.3	12	120 Card Edge DIMM
EDI2KG464128V15D*	4x128Kx64	3.3	15	120 Card Edge DIMM

*Consult Factory for Availability

Package Description

120 Lead
Card Edge DIMM